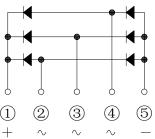






# **Three Phase Bridge Rectifiers**





#### **Features**

- UL recognition, file #E230084
- Thin single in-line package
- Glass passivated chip junction
- High surge current capability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

### **Typical Applications**

General purpose use in AC/DC bridge full wave rectification for Server、Frequency converter、Industrial power supply.

#### **Mechanical Data**

• Package: 3GBJ

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant

• Terminals: Tin plated leads, solderable per

J-STD-002 and JESD22-B102

• Polarity: As marked on body

### ■Maximum Ratings (Ta=25°C Unless otherwise specified)

| = Waximum Natings (1a 20 0 offices offices opening)                              |                              |                  |                  |            |          |           |           |  |
|--|------------------------------|------------------|------------------|------------|----------|-----------|-----------|--|
| PARAMETER  |                              | SYMBOL           | UNIT             | DG50NA60   | DG50NA80 | DG50NA100 | DG50NA120 |  |
| Device marking code  |                              |                  |                  | DG50NA60   | DG50NA80 | DG50NA100 | DG50NA120 |  |
| Maximum Repetitive Peak Reverse Voltage  |                              | VRRM             | ٧                | 600        | 800      | 1000      | 1200      |  |
| Maximum RMS Voltage  |                              | VRMS             | V                | 420        | 560      | 700       | 840       |  |
| Maximum DC blocking Volta  | age                          | VDC              | V                | 600        | 800      | 1000      | 1200      |  |
| Average rectified output  With heatsink Tc =95°C                                 |                              | lo.              |                  | 50.0       |          |           |           |  |
| current<br>@60Hz sine wave, R-load   | Without heatsink<br>Ta =25°C | lO               | Α                | 5.0        |          |           |           |  |
| Forward Surge Current (Non-repetitive)<br>@8.3ms Half-sine wave,1 cycle, Tj=25°C |                              |                  | А                | 500        |          |           |           |  |
| Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, Ti=25°C       |                              | IFSM             |                  | 1000       |          |           |           |  |
| Current squared time<br>@1ms≤t≤8.3ms Tj=25°C, Rating of per diode                |                              | l²t              | A <sup>2</sup> s | 1037.5     |          |           |           |  |
| Storage temperature  |                              | T <sub>stg</sub> | °C               | -55 ~ +150 |          |           |           |  |
| Junction temperature   |                              | Tj               | °C               | -55 ~ +150 |          |           |           |  |
| Dielectric strength @ Terminals to case, AC 1 minute                             |                              | Vdis             | KV               | 2.5        |          |           |           |  |
| Mounting torque<br>@Recommend torque: 5kg·cm                                     |                              | Tor              | kg∙cm            | 8          |          |           |           |  |

# **DG50NA60 THRU DG50NA120**

### **■Electrical Characteristics** (Ta=25°C Unless otherwise specified)

| PARAMETER   | SYMBOL | UNIT | TEST CONDITIONS   | DG50NA60 | DG50NA80 | DG50NA100 | DG50NA120 |
|---|--------|------|---|----------|----------|-----------|-----------|
| Maximum instantaneous forward voltage drop per diode    | VF     | ٧    | IFM=25A 1.1   |          |          |           |           |
| Maximum DC reverse current at rated DC blocking voltage | IR     | μА   | T <sub>j</sub> =25°C  | 5        |          |           |           |
| per diode   |        |      | T <sub>j</sub> =125°C 200                                       |          |          |           |           |
| Typical junction capacitance                            | Cj     | pF   | Measured at 1MHz<br>and Applied Reverse<br>Voltage of 4.0 V.D.C |          |          |           |           |

# **■Thermal Characteristics** $(T_a=25$ $^{\circ}$ C Unless otherwise specified)

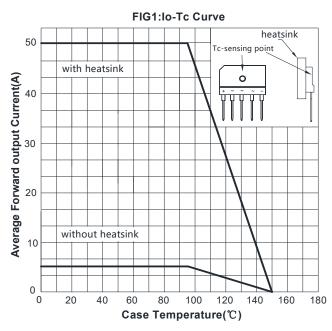
| PARAMETER             |   | SYMBOL             | UNIT | DG50NA60 | DG50NA80 | DG50NA100 | DG50NA120 |
|-----------------------|---|--------------------|------|----------|----------|-----------|-----------|
| Typical               | Between junction and ambient,<br>Without heatsink | RθJ-A              | °C/W | 18.0     |          |           |           |
| Thermal<br>Resistance | Between junction and case,<br>With heatsink       | R <sub>0</sub> J-C | C/VV | 0.5      |          |           |           |

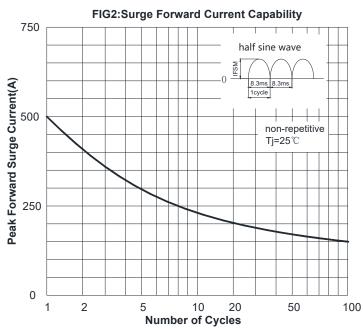
Note: Device mounted on 75mm x 45mm x 5.5mm Aluminum Plate Heatsink.

### **■Ordering Information** (Example)

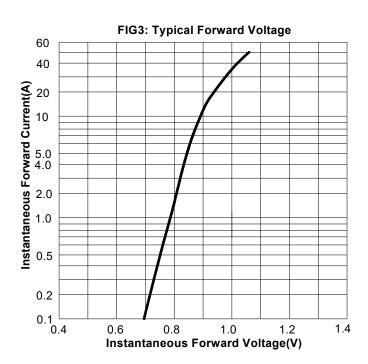
| PREFERED P/N         | PACKING<br>CODE | UNIT WEIGHT(g) | MINIIMUM<br>PACKAGE(pcs) | INNER BOX QUANTITY(pcs) | OUTER CARTON QUANTITY(pcs) | DELIVERY MODE |
|----------------------|-----------------|----------------|--------------------------|-------------------------|----------------------------|---------------|
| DG50NA60 ~ DG50NA120 | A1              | Approximate 10 | 100                      | 100                     | 1000                       | вох           |
| DG50NA60 ~ DG50NA120 | B1              | Approximate 10 | 10                       | 1                       | 1000                       | TUBE          |

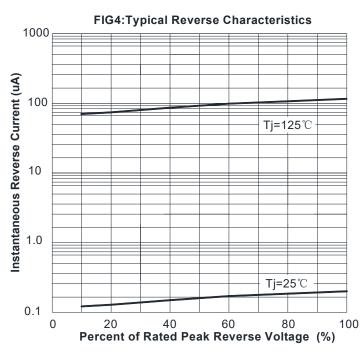
### **■ Characteristics** (Typical)



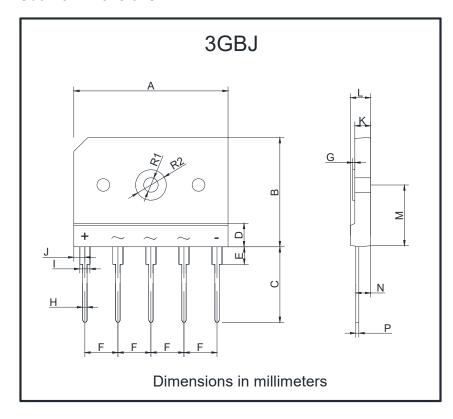


# **DG50NA60 THRU DG50NA120**





#### **■** Outline Dimensions



| 3GBJ |      |      |  |  |  |  |
|------|------|------|--|--|--|--|
| Dim  | Min  | Max  |  |  |  |  |
| Α    | 34.7 | 35.3 |  |  |  |  |
| В    | 24.7 | 25.3 |  |  |  |  |
| С    | 17.0 | 17.6 |  |  |  |  |
| D    | 5.6  | 6.2  |  |  |  |  |
| E    | 3.8  | 4.4  |  |  |  |  |
| F    | 7.2  | 7.8  |  |  |  |  |
| G    | 0.4  | 0.6  |  |  |  |  |
| Н    | 0.9  | 1.1  |  |  |  |  |
| I    | 2.2  | 2.4  |  |  |  |  |
| J    | 2.2  | 2.6  |  |  |  |  |
| K    | 3.4  | 3.8  |  |  |  |  |
| L    | 4.4  | 4.8  |  |  |  |  |
| М    | 13.9 | 14.5 |  |  |  |  |
| N    | 3.15 | 3.65 |  |  |  |  |
| Р    | 0.65 | 0.75 |  |  |  |  |
| R1   | 2.7  | 3.7  |  |  |  |  |
| R2   | 6.7  | 7.3  |  |  |  |  |



## **DG50NA60 THRU DG50NA120**

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